SUB**STRATE PROCESSING DEVICE, SEMICONDUCTOR DEVICE PRODUCTION METHOD, AND PROGRAM**

[ABSTRACT]

The present invention enhances the uniformity, within and between substrate surfaces, of a film formed on a substrate. In the present invention, first and third gas supply parts extend vertically along a substrate holding tool and have tubular nozzles each having a plurality of gas supply holes formed therein such that the upper end of the gas supply hole, from among the plurality of gas supply holes, that is formed furthest to the top of the nozzle is disposed so as to correspond to an uppermost dummy wafer supported in an upper dummy wafer support area and the lower end of the gas supply hole, from among the plurality of gas supply holes, that is formed furthest to the bottom of the nozzle is disposed so as to correspond to a lowermost dummy wafer supported in a lower dummy wafer support area. A second gas supply part extends vertically along the substrate holding tool and has a tubular nozzle having, formed therein, a gas supply port comprising a plurality of gas supply holes or a slit-like opening part. The gas supply port opens at least toward a product wafer support area.

FIGS. 4A and 4B